

Attorney Do ket # 10961260-2

REPLACEMENT CLAIMS

1. (Amended) A semiconductor isolation structure comprising:
- a substrate, the substrate comprising a surface;
  - a first device and a second device formed within the substrate;
  - an isolation region formed within the substrate between the first device and the second device, the isolation region comprising:
    - a single deep region which extends into the substrate, the deep region comprising a deep region cross-sectional area, the deep region abutting only the substrate and a single shallow region;
    - said* a single shallow region which extends to the surface of the substrate, the shallow region comprising: *extending*
      - a protective outer wall adjacent to the substrate;
      - an inner sealing wall located exclusively within the shallow region and adjacent to the protective outer wall: and
      - the shallow region having a shallow region cross-sectional area; wherein the deep region cross-sectional area is greater than the shallow region cross-sectional area.

5. (Amended) A semiconductor isolation structure comprising:
- a substrate, the substrate comprising a surface;
  - a first device and a second device formed within the substrate;
  - an isolation region formed within the substrate between the first device and the second device, the isolation region comprising:
    - a single deep region which extends into the substrate, the deep region comprising an oxide, the deep region abutting only <sup>the</sup> substrate and a single shallow region;
    - said* a single shallow region which extends to the surface of the substrate, the shallow region comprising: *extending*
      - a protective outer wall adjacent to the substrate,
      - an inner sealing wall located exclusively within the shallow region and adjacent to the protective outer wall.

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